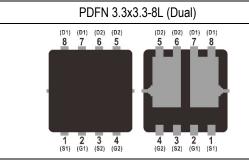


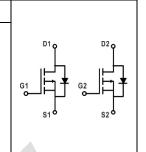
100V Dual N-CHANNEL Power MOSFET

**V<sub>DSS</sub>**, 100V

 $R_{DS(ON)}$  ,  $270m\Omega$  (max.) @  $V_{GS}{=}10V$   $R_{DS(ON)}$  ,  $300m\Omega$  (max.) @  $V_{GS}{=}4.5V$ 

 $I_D$  , 5.6A





## **Description**

The SGD1011ED uses advanced trench technology MOSFETs to provide excellent  $R_{\text{DS(ON)}}$  and low gate charge.

The complementary Power MOSFETs may be used in H-bridge, Inverters and other applications.

#### **Features**

- Low On-Resistance
  - Low Input Capacitance
- Low Miller Charge
- Low Input/Output Leakage
- · Pb-free lead plating; RoHS compliant

## **Applications**

- Motor / Body Load Control
- Automotive Systems
- Load Switch

**Ordering Information** 

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGD1011ED	Halogen-Free	PDFN 3.3x3.3-8L (Dual)	ED	Tape & Reel	5,000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Dunin Courset Continuous	T <sub>C</sub> =25°C		5.6	А
Drain Current-Continuous	Tc=100°C	lb	3.5	А
Drain Current-Pulsed Note 1		I <sub>DM</sub>	22	А
Mayimum Dayyar Dissination	Tc=25°C	D	12.5	W
Maximum Power Dissipation	Tc=100°C	P <sub>D</sub>	5	W
Operating Junction Temperature Range		T <sub>J</sub> T <sub>STG</sub>	-55 to +150	°C

**Thermal Resistance Ratings** 

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	RθJA	Steady State	-	-	75	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	10	°C/W



100V Dual N-CHANNEL Power MOSFET

## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =250µA	100	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250µA	1	-	2.5	V
Drain-Source On-State Resistance	В	V <sub>GS</sub> =10V, I <sub>DS</sub> =3A	-	-	270	
Dialii-Source Oii-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>DS</sub> =2A	-		300	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	497	-	
Output Capacitance	Coss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz		28	-	pF
Reverse Transfer Capacitance	Crss		7	16	-	
Forward Transconductance	gfs	V <sub>D</sub> =5V, I <sub>D</sub> =2A	-	5	-	S

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	$T_{d(on)}$		-	5	-	
Rise Time	tr	$V_{DD}$ =50V, $V_{GS}$ =10V, $R_{G}$ =3.3 $\Omega$ ,	-	6.8	-	
Turn-Off Delay Time	T <sub>d(off)</sub>	I <sub>D</sub> =2A	-	14.6	-	ns
Fall Time	tf		-	1.8	-	
Total Gate Charge at -4.5V	$Q_g$	V -20V V -4.5V	-	9.5	-	
Gate to Source Gate Charge	Qgs	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	-	1.5	-	nC
Gate to Drain "Miller" Charge	$Q_{gd}$	10-2A	-	1.6	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A	-	-	1.2	V
Continuous Source Current	Is	V =V =0V Force Current	-	-	5.6	Α
Pulsed Source Current	I <sub>SM</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	=	-	22	Α

## Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Rejah is guaranteed by design while Rech is determined by the user's board design. Rejah shown below for single device operation on FR-4 in still air.



# SGD1011ED 100V Dual N-CHANNEL Power MOSFET

## **Marking Information**

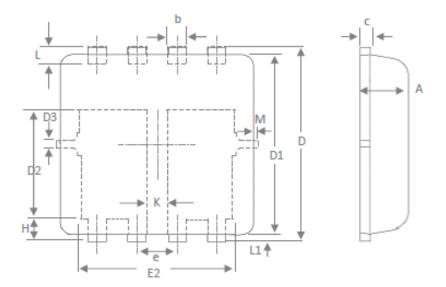
PDFN 3.3x3.3-8L(Dual) (ED)	Marking Rule	
Laser Marking  1011ED  YMMXXX  Diagram	Line 1: Device Name 1011ED Line 2: Date Code YMMXXX  Y: Year Code MM: Month Code XXX: Serial Number  Year Code Description As Below	

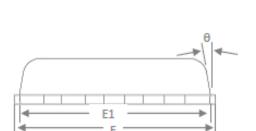
# Year Code Description

Year Code	Year		
0	2010	2020	
1	2011	2021	
2	2012	2022	
3	2013	2023	
4	2014	2024	
5	2015	2025	
6	2016	2026	
7	2017	2027	
8	2018	2028	
9	2019	2029	









Symbol	Min	Nor	Max
Α	0.70	0.75	0.80
b	0.25	0.30	0.35
С	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	-	0.13	-
Е	3.00	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
е		0.65BSC	
Н	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
K	0.30	-	-
θ	-	10°	12°
М	-	-	0.15

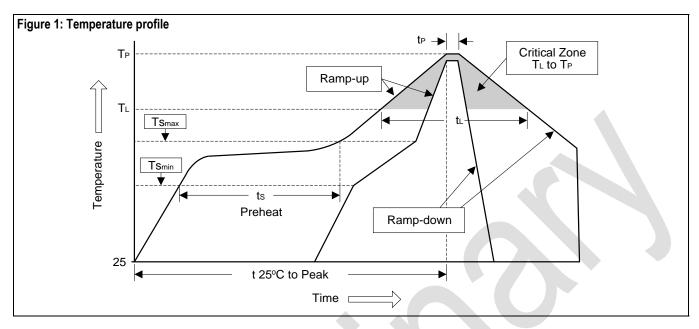
- 1. All dimension are in millimeters.
- 2. Dimension does not include burrs and mold flash/protrusions.



100V Dual N-CHANNEL Power MOSFET

## Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly	
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	<3°C/sec	<3°C/sec	
Preheat			
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C	
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C	
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec	
Tsmax to T∟			
- Ramp-up Rate	<3°C/sec	<3°C/sec	
Time maintained above:			
- Temperature (T∟)	183°C	217°C	
- Time (t∟)	60 to 150 sec	60 to 150 sec	
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C	
Time within 5°C of actual Peak Temperature (t⊳)	10 to 30 sec	20 to 40 sec	
Ramp-down Rate	<6°C/sec	<6°C/sec	
Time 25°C to Peak Temperature	<6 minutes	<8 minutes	

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



100V Dual N-CHANNEL Power MOSFET

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